

PRODUCT SPECIFICATION

Model No.: FYL-3014PTB2G01-SO-WG

Descriptions:

- Emitting Color: NPN silicon phototransistor.
- Device Outline: $\Phi 3\text{mm}$ round type.
- Lens Type: Deep blue.



CUSTOMER APPROVED SIGNATURES	APPROVED BY	SALES BY	PREPARED BY
			

NINGBO FORYARD OPTOELECTRONICS CO.,LTD.

Add:No. 666 Jinghua Road, Hi-tech Park, Ningbo, Zhejiang, China

Zip:315103

Tel: 0086-574-87933652 87927870

Fax: 0086-574-87927917

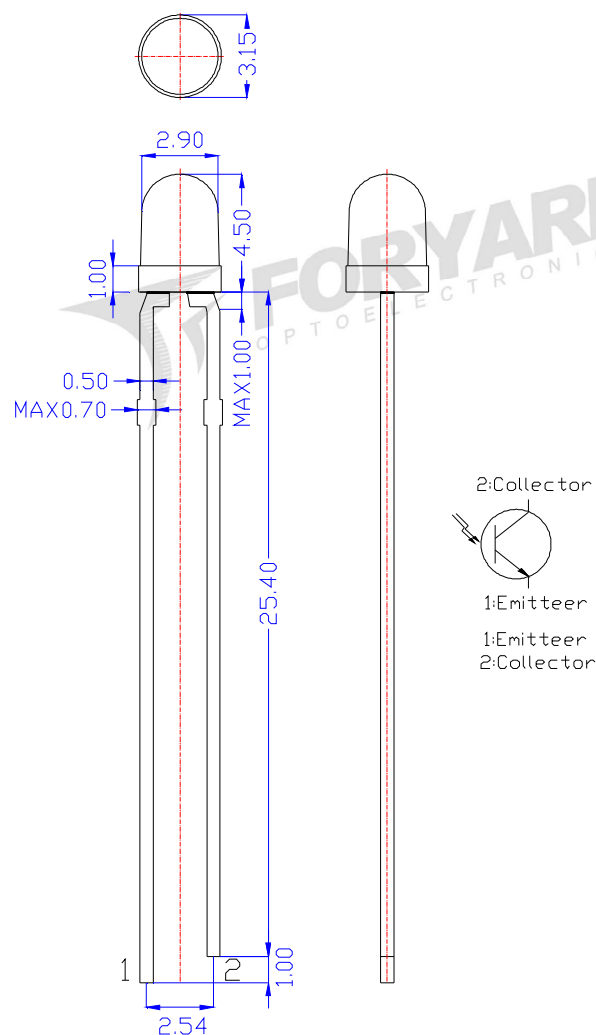
E-mail:Sales@foryard.com (General)

Model No.: FYL-3014PTB2G01-SO-WG

■ Features

- 1.Low power consumption.
- 2.High efficiency.
- 3.General purpose leads.
- 4.High intensity.
- 5.RoHs compliant.

■ Package configuration



Notes:

1. All dimensions are millimeters (inches)
2. Tolerance is $\pm 0.25\text{mm}$ (.010") unless otherwise noted.
3. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.
4. The drawing is different from the actual one, please refer to the sample.

Model No.: FYL-3014PTB2G01-SO-WG

■ Absolute Maximun Ratings(Ta=25°C)

Parameter	Symbol	Ratings	Unit
Power Dissipation(below 25 Free Air Temperature)	Pd	75	mW
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Collector Voltage	V _{ECO}	5	V
Collector Current	I _{C(ON)}	20	mA
Operating Temperature	T _{opr}	-25~85	°C
Storage Temperature	T _{str}	-40~100	°C
Lead Soldering Temperature(2mm form body for 5 seconds)	Tsol	260	°C

■ Typical Electrical &Optical Charcteristics(Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Test Condition	Unit
Collector-Emitter Breakdown Voltage	BV _{CEO}	30	---	---	I _C =100μA Ee=0mW/cm ²	V
Emitter-Collector Breakdown Voltage	BV _{ECO}	5	---	---	I _C =100μA Ee=0mW/cm ²	V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	---	---	0.4	I _C =2mA Ee=1mW/cm ²	V
Rise Time	t _r	---	15	--	V _{CE} =5V I _C =1mA R _L =1000Ω	μS
Fall Time	t _f	---	15	--		
Collector Dark Current	I _{CEO}	---	---	100	Ee=0mW/cm ² V _{CE} =20V	nA
On State Collector Current	I _{C(ON)}	0.95	---	4.85	Ee=1mW/cm ² V _{CE} =5V	mA
Rang of Spectral Bandwidth	λ _{0.5}	760	--	1100	--	nm
Wavelength of Peak Sensitivity	λ _p	---	940	--	--	nm

Note:

- 1.Luminous Intensity is based on the Foryard standards.
- 2.Pay attention about static for InGaN

■ Rank

Code	G	H	J	K
On State Collector Current(mA)	0.95~1.60	1.45~2.25	2.1~3.2	3.1~4.85

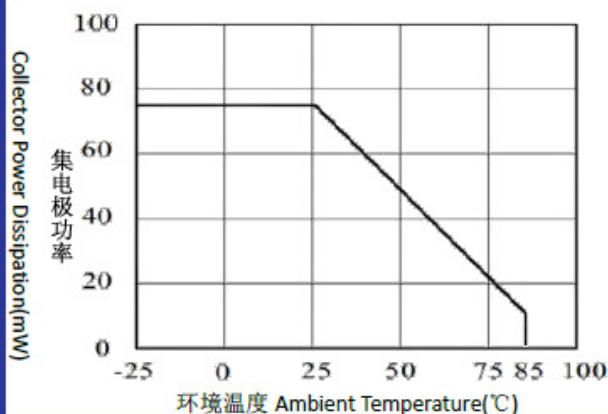
Ee=1mW/cm² V_{CE}=5V

Model No.: FYL-3014PTB2G01-SO-WG

Typical Electro-Optical Characteristics Curves

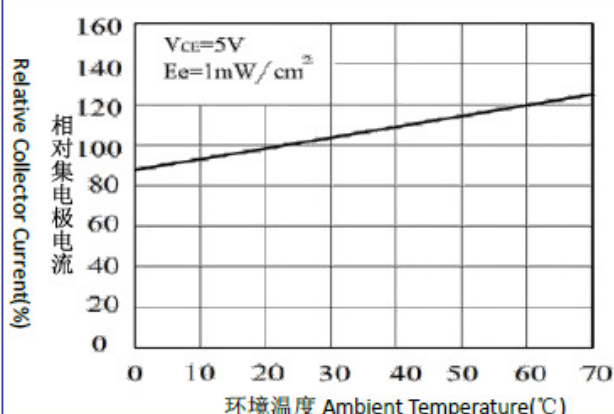
集电极功率与环境温度的关系

Collector Power Dissipation vs. Ambient Temperature



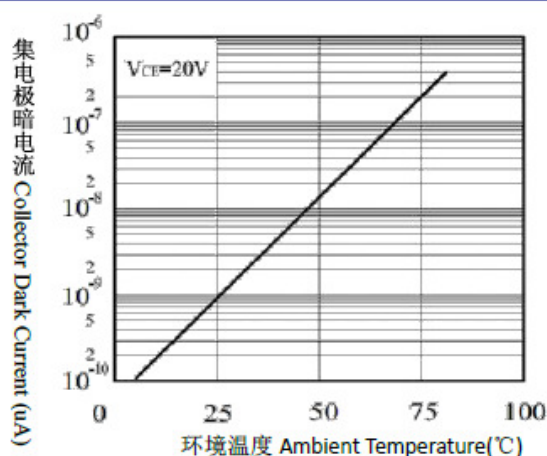
相对集电极电流与环境温度的关系

Relative Collector Current vs. Ambient Temperature



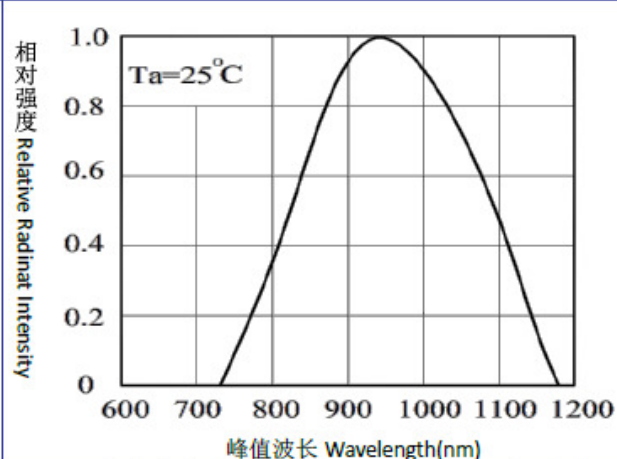
集电极暗电流与环境温度的关系

Collector Dark Current vs. Ambient Temperature



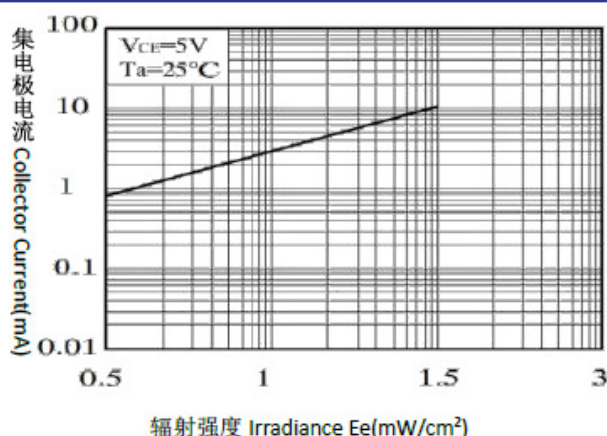
感应波长曲线图

Spectral Sensitivity



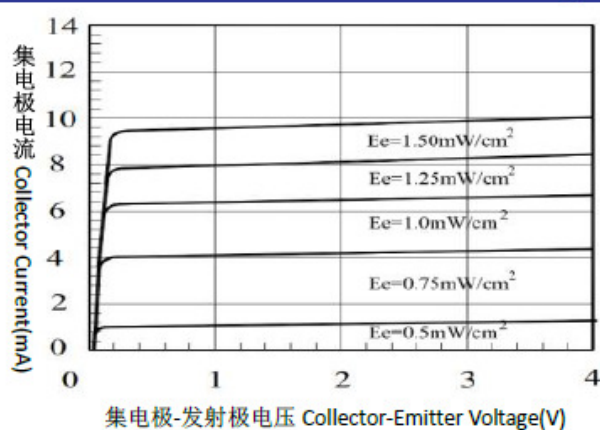
集电极电流与辐射强度的关系

Collector Current vs. Irradiance



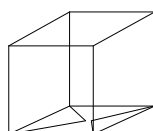
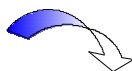
集电极电流与集电极-发射极电压的关系

Collector Current vs. Collector-Emitter Voltage

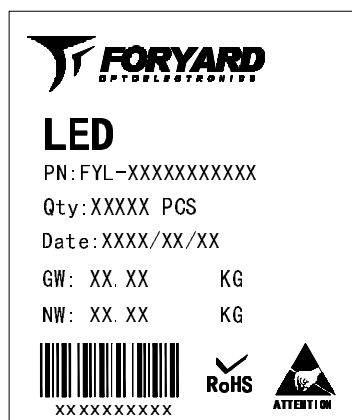
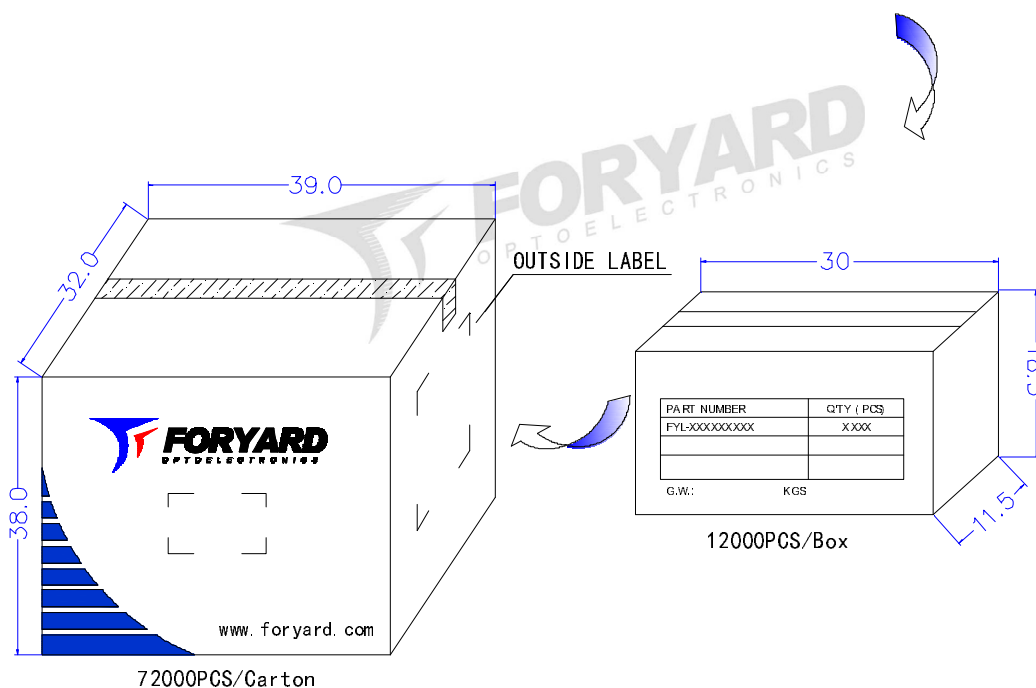


Model No.: FYL-3014PTB2G01-SO-WG

■ LAMP PACKING.



3mm 1000PCS/Polybag



OUTSIDE LABEL

Note: The specifications are subject to change without notice. Please contact us for updated information.